### Silicon N-Channel MOS FET

# **HITACHI**

#### **Application**

Low frequency power amplifier

Complementary pair with 2SJ160, 2SJ161 and 2SJ162

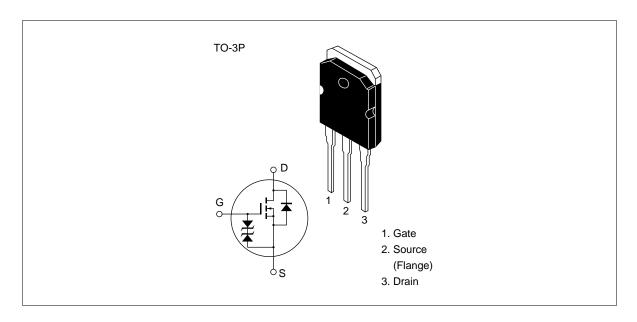
#### **Features**

- · Good frequency characteristic
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes
- Suitable for audio power amplifier



## <u>2SK1056, 2SK1057, 2SK1058</u>

#### Outline



#### **Absolute Maximum Ratings** $(Ta = 25^{\circ}C)$

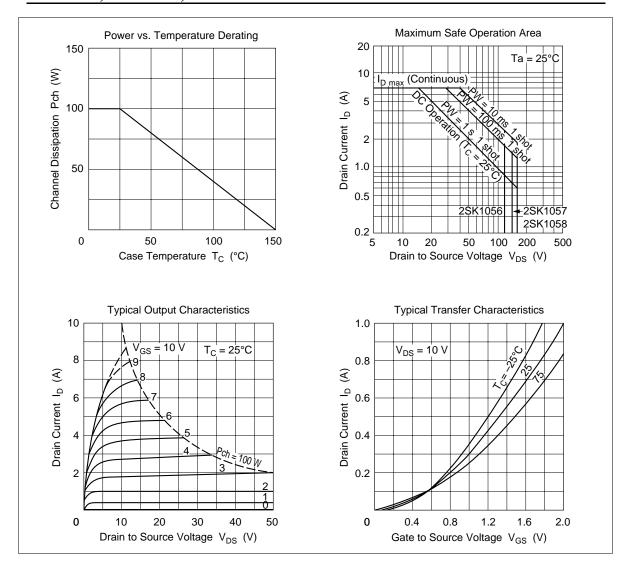
Item		Symbol	Ratings	Unit
Drain to source voltage 2SK1056		$V_{\scriptscriptstyle DSX}$	120	V
	2SK1057		140	
	2SK1058		160	
Gate to source voltage		V <sub>GSS</sub>	±15	V
Drain current		I <sub>D</sub>	7	A
Body to drain diode reverse drain current		I <sub>DR</sub>	7	А
Channel dissipation		Pch*1	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

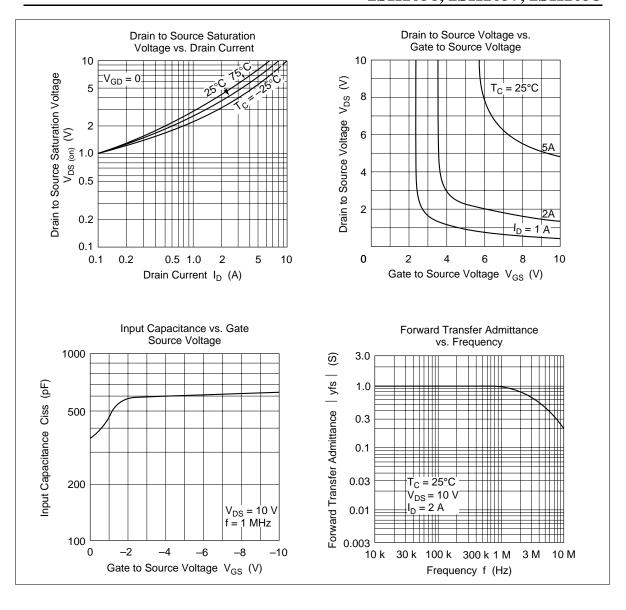
Note: 1. Value at  $T_c = 25^{\circ}C$ 

#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

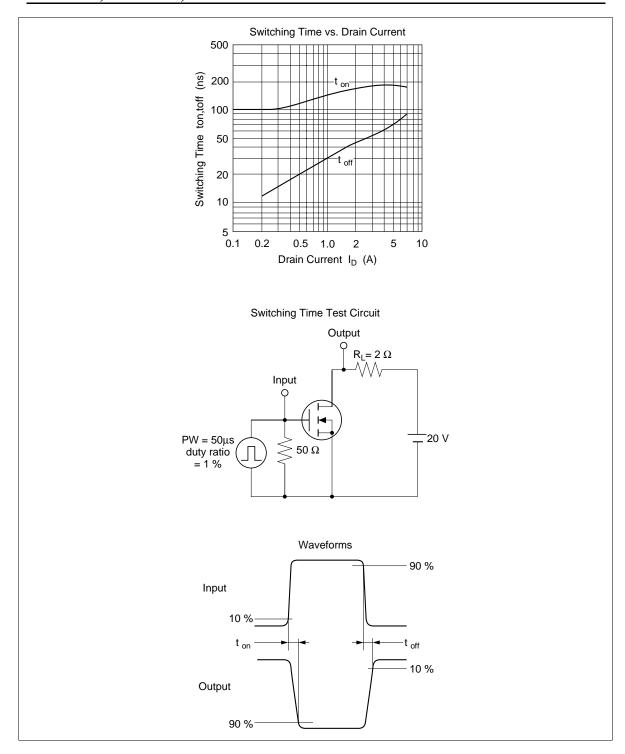
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Item		Symbol	Min	Тур	Max	Unit	Test conditions
	Drain to source	2SK1056	$V_{(BR)DSX}$	120	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = -10 \text{ V}$
Gate to source breakdown voltage $V_{(BR)GSS}$ $\pm 15$ $  V$ $I_{G} = \pm 100 \mu\text{A},  V_{DS} = 0$ Gate to source cutoff voltage $V_{GS(off)}$ 0.15 $-$ 1.45 $V$ $I_{D} = 100 \text{mA},  V_{DS} = 10 V$ Drain to source saturation $V_{DS(sat)}$ $-$ 12 $V$ $I_{D} = 7 \text{A},  V_{GD} = 0 ^{*1}$ voltage Forward transfer admittance $ \text{yfs} $ 0.7 1.0 1.4 $S$ $I_{D} = 3 \text{A},  V_{DS} = 10 V ^{*1}$ Input capacitance $Ciss$ $-$ 600 $-$ pF $V_{GS} = -5 V,  V_{DS} = 10 V,$ Output capacitance $Coss$ $-$ 350 $-$ pF $I_{DS} = 10 \text{MHz}$	breakdown voltage	2SK1057	_	140	_			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		2SK1058	_	160	_			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		kdown	$V_{(BR)GSS}$	±15	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
	Gate to source cutof	f voltage	$V_{GS(off)}$	0.15	_	1.45	V	$I_D = 100 \text{ mA}, V_{DS} = 10 \text{ V}$
Input capacitance Ciss — 600 — pF $V_{GS} = -5 \text{ V}, V_{DS} = 10 \text{ V},$ Output capacitance Coss — 350 — pF $f = 1 \text{ MHz}$		ration	V <sub>DS(sat)</sub>	_	_	12	V	$I_D = 7 \text{ A}, V_{GD} = 0 *1$
Output capacitance Coss — 350 — pF f = 1 MHz	Forward transfer add	mittance	yfs	0.7	1.0	1.4	S	$I_D = 3 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
	Input capacitance		Ciss	_	600	_	pF	$V_{GS} = -5 \text{ V}, V_{DS} = 10 \text{ V},$
Reverse transfer capacitance Crss — 10 — pF	Output capacitance		Coss	_	350	_	pF	f = 1 MHz
·	Reverse transfer cap	pacitance	Crss	_	10	_	pF	
Turn-on time $t_{on}$ — 180 — ns $V_{DD} = 20 \text{ V}, I_D = 4 \text{ A},$	Turn-on time		t <sub>on</sub>	_	180	_	ns	$V_{DD} = 20 \text{ V}, I_{D} = 4 \text{ A},$
Turn-off time $t_{\text{off}}$ — 60 — ns	Turn-off time		t <sub>off</sub>		60	_	ns	

Note: 1. Pulse test

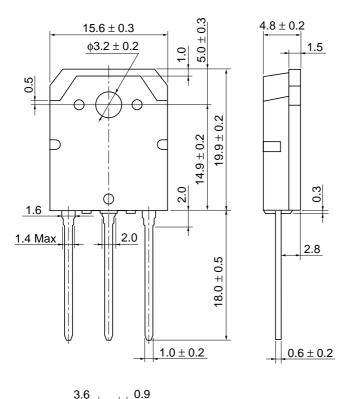


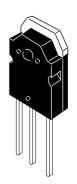


## <u>2SK1056, 2SK1057, 2SK1</u>058



Unit: mm





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5.45 ± 0	0.5					5.4	45 ±	0.5

Hitachi Code	TO-3P
JEDEC	
EIAJ	Conforms
Weight (reference value)	5.0 g

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# IITACH

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Öhte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive. San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group D-85622 Feldkirchen, Munich Germany

Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd.

Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281

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Telex: 40815 HITEC HX